

SuperMOS – SOT-23 -30V BV_{DSS} , 46m Ω $R_{DS(on)}$, P-channel MOSFET

1. Description

The BSS308PEH6327-ES is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product BSS308PEH6327-ES is Pb-free.

2. Features

- 30V, $R_{DS(ON)}=46m\Omega$ (Typ.) @ $V_{GS}=-10V$
 $R_{DS(ON)}=62m\Omega$ (Typ.) @ $V_{GS}=-4.5V$
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
BSS308PEH6327-ES	SOT-23	R7	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

Table-1 Ordering information

5. Pin Configuration and Functions

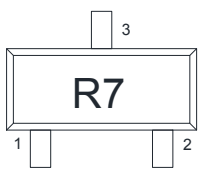
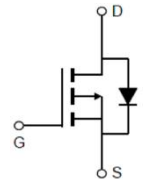
Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	BV_{DSS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$T_A=25^\circ\text{C}$	-3.8	A
	$T_A=75^\circ\text{C}$	-2.9	
Maximum Power Dissipation	$T_A=25^\circ\text{C}$	1.4	W
Pulsed Drain Current	I_{DM}	-15.2	A
Operating Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$		90	°C/W

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			-1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.9	-1.5	-2.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-3A$		46	60	m Ω
		$V_{GS}=-4.5V, I_D=-3A$		62	80	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=-15V,$ $f=1MHz$		550		pF
Output Capacitance	C_{OSS}			75		
Reverse Transfer Capacitance	C_{RSS}			63		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=-10V, V_{DS}=-15V,$ $I_D=-4A$		6.5		nC
Gate-to-Source Charge	Q_{GS}			1.1		
Gate-to-Drain Charge	Q_{GD}			1.3		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=-10V, V_{DS}=-15V,$ $R_L=3.5\Omega, R_G=3\Omega$		14		ns
Rise Time	t_r			60		
Turn-Off Delay Time	$t_{d(OFF)}$			19		
Fall Time	t_f			11		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-1.0A$		-0.7	-1.5	V

7. Typical Characteristic

Figure 1. On-Regin Characteristics

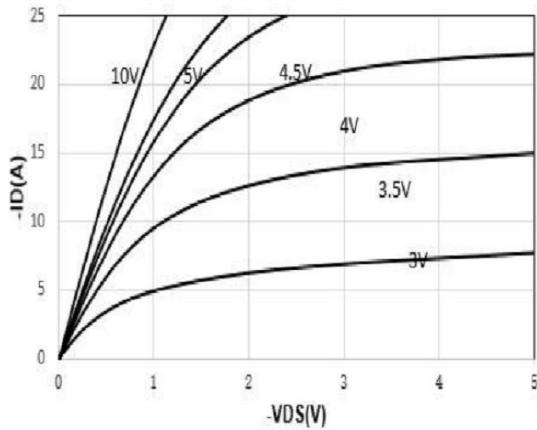


Figure 2. Transfer Characteristics

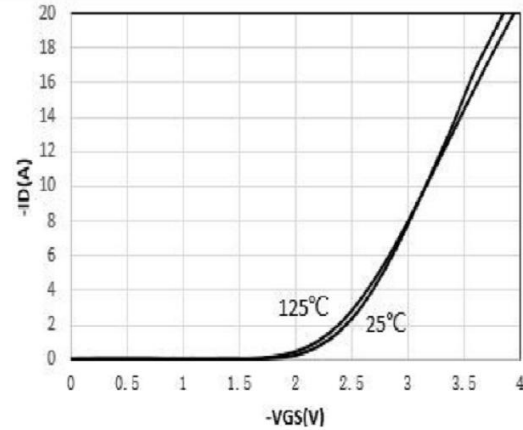


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

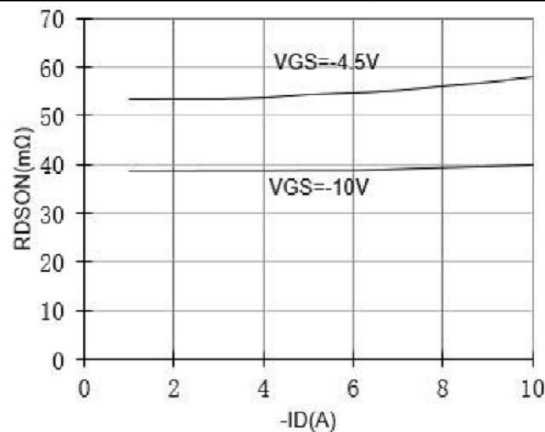


Figure 4. On-Resistance vs. Junction Temperature

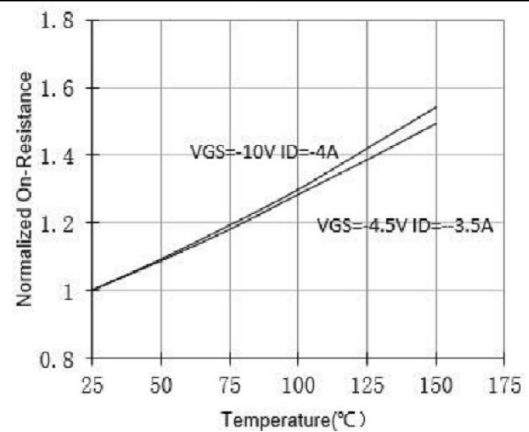


Figure 5. On-Resistance vs. Gate-Source Voltage

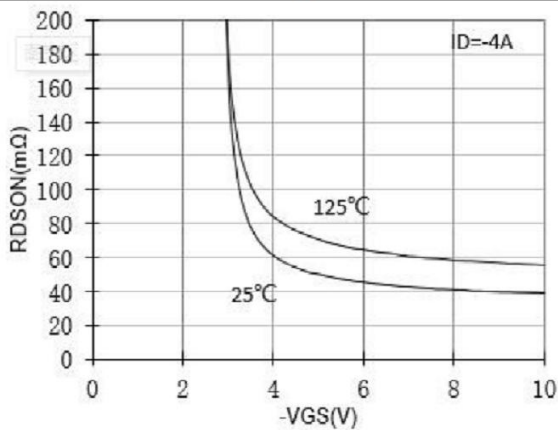
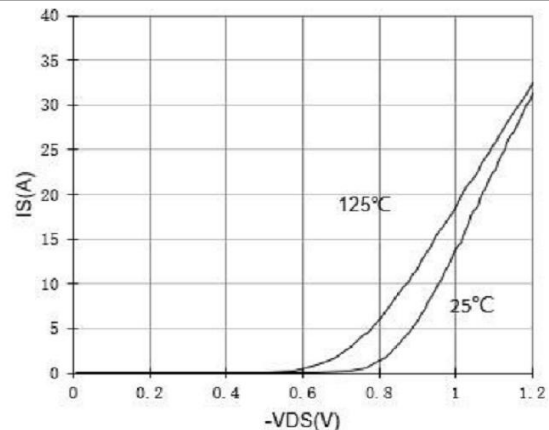


Figure 6. Body-Diode Characteristics



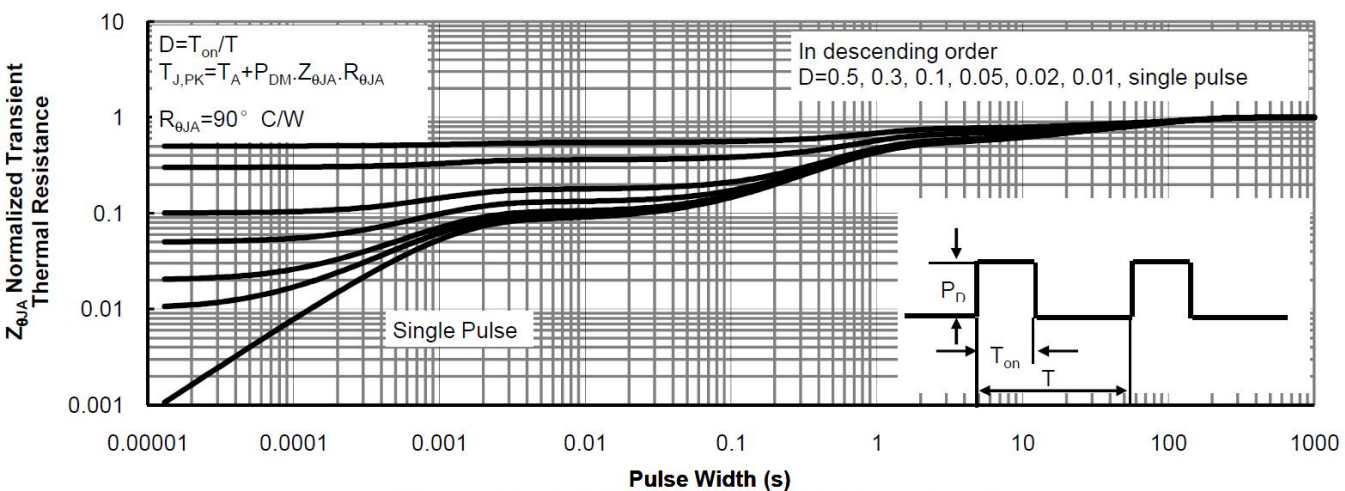
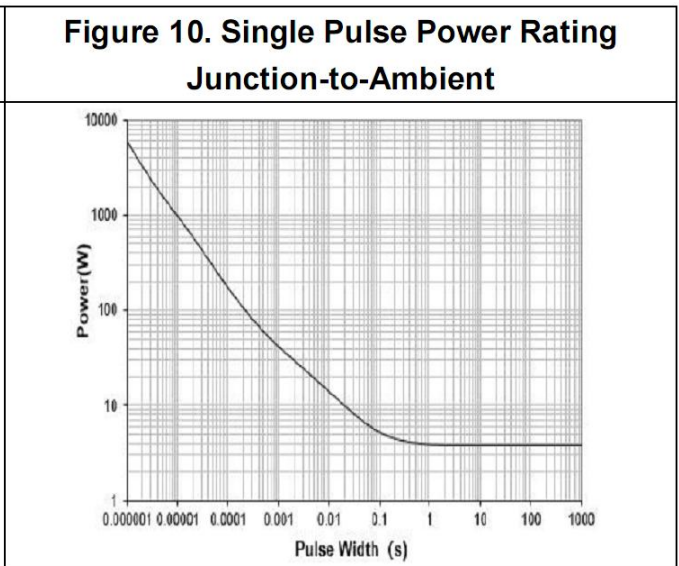
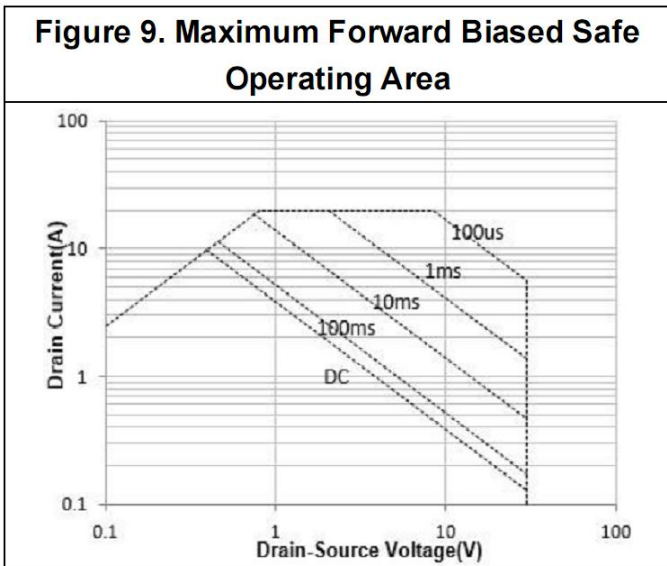
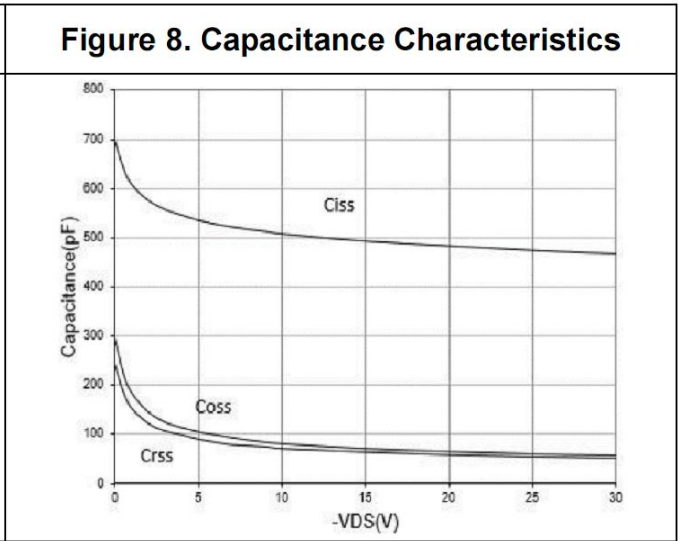
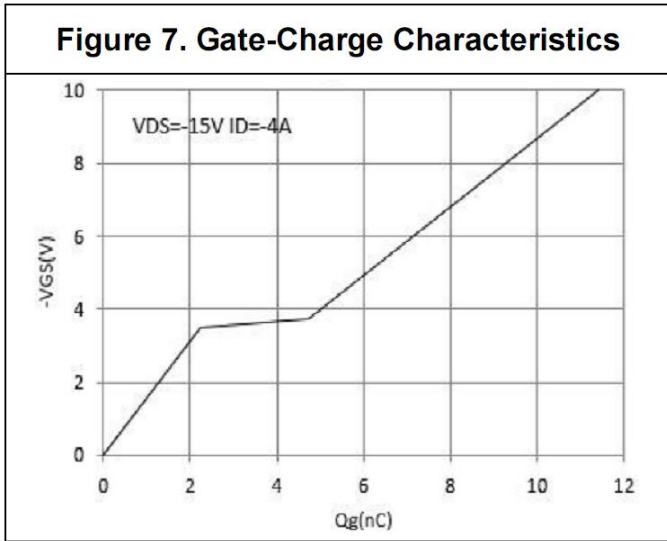
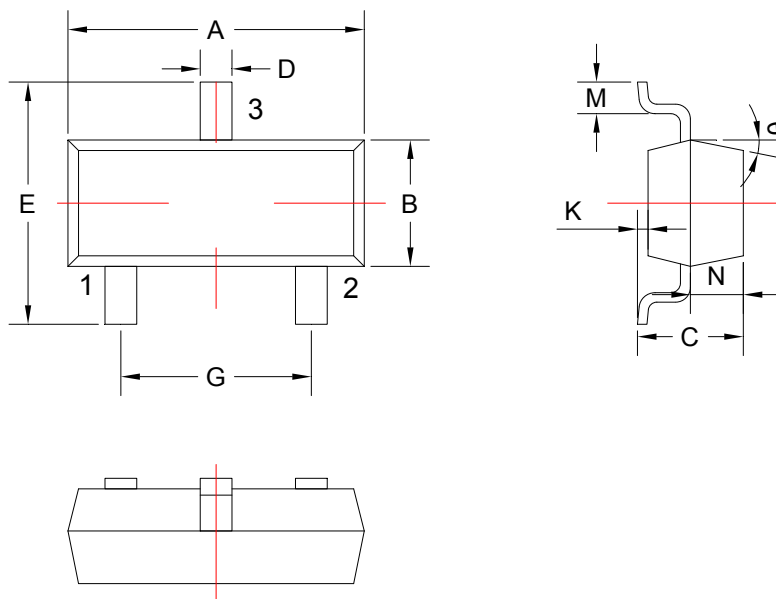


Figure 11: Normalized Maximum Transient Thermal Impedance

8. Dimension (SOT-23)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.85	3.04	G	1.80	2.00
B	1.20	1.40	K	0	0.10
C	0.90	1.10	M	0.20	-
D	0.40	0.50	N	0.50	0.70
E	2.25	2.55	θ	5°	9°

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